CAT64LC20/CAT64LC20I

2K-Bit SERIAL E2PROM

FEATURES

- **■** SPI Bus Compatible
- Low Power CMOS Technology
- 2.5V to 5.5V Operation
- Self-Timed Write Cycle with Auto-Clear
- Hardware Reset Pin
- Hardware and Software Write Protection

- Power-Up Inadvertant Write Protection
- RDY/BUSY Pin for End-of-Write Protection
- 100,000 Program/Erase Cycles
- 100 Year Data Retention
- **ZERO Power™ (CAT64LC20Z) Version Available**
- Optional High Endurance Device Available

DESCRIPTION

The CAT64LC20 and CAT64LC20I are 2K bit Serial E²PROM memory devices which are configured as 128 registers by 16 bits. Each register can be written (or read) serially by using the DI (or DO) pin. The CAT64LC20/CAT64LC20I is manufactured using

Catalyst's advanced CMOS E²PROM floating gate technology. It is designed to endure 100,000 program/erase cycles and has a data retention of 100 years. The device is available in 8 pin DIP or SO packages.

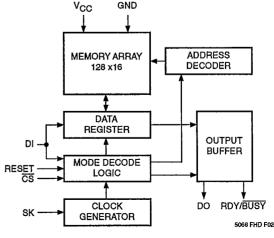
PIN CONFIGURATION

| DIP Package | SO Pac | kage J | SO Paci | cage S |
|--|---|-------------------------|---------------------------------------|--------|
| CS •1 8 VCC SK 2 7 RDY/BUSY DI 3 6 RESET DO 4 5 GND | RDY/BUSY -1 V _{CC} - 2 CS - 3 SK - 4 | 8 RESET 7 GND 6 DO 5 DI | CS [•1 SK [2 DI [3 DO [4 | 8 |

PIN FUNCTIONS

| Pin Name | Function |
|----------|-----------------------------|
| CS | Chip Select |
| SK | Clock Input |
| DI | Serial Data Input |
| DO | Serial Data Output |
| Vcc | +2.5V to +5.5V Power Supply |
| GND | Ground |
| RESET | Reset |
| RDY/BUSY | Ready/BUSY Status |

BLOCK DIAGRAM



TD 5066

CATALYST SEMICONDUCTOR

ABSOLUTE MAXIMUM RATINGS*

*COMMENT

| Temperature Under Bias | 55°C to +125°C |
|---|---------------------------------|
| Storage Temperature | 65°C to +150°C |
| Voltage on any Pin with Respect to Ground ⁽¹⁾ | -2.0V to +V _{CC} +2.0V |
| Vcc with Respect to Ground | 2.0V to +7.0V |
| Package Power Dissipation Capability (Ta = 25°C) | 1.0W |
| Lead Soldering Temperature (10 s | ecs)300°C |
| Output Short Circuit Current(2) | 100 mA |
| | |

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

Advance

RELIABILITY CHARACTERISTICS

| Symbol | Parameter | Min. | Max. | Units | Reference Test Method |
|-------------------------|--------------------|---------|------|-------------|-------------------------------|
| N _{END} (3) | Endurance | 100,000 | | Cycles/Byte | MIL-STD-883, Test Method 1033 |
| T _{DR} (3) | Data Retention | 100 | | Years | MIL-STD-883, Test Method 1008 |
| V _{ZAP} (3) | ESD Susceptibility | 2000 | | Volts | MIL-STD-883, Test Method 3015 |
| I _{LTH} (3)(4) | Latch-Up | 100 | | mA | JEDEC Standard 17 |

CAPACITANCE ($T_A = 25$ °C, f = 1.0 MHz, $V_{CC} = 5.5$ V)

| Symbol | Test | Max. | Units | Conditions |
|---------------------|---|------|-------|-----------------------|
| CI/O(3) | Input/Output Capacitance (DO, RDY/BUSY) | 8 | рF | V _{I/O} = 0V |
| C _{IN} (3) | Input Capacitance (CS, SK, DI, RESET) | 6 | pF | V _{IN} = 0V |

Note:

(2) Output shorted for no more than one second. No more than one output shorted at a time.

(3) This parameter is tested initially and after a design or process change that affects the parameter.

⁽¹⁾ The minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods of less than 20 ns. Maximum DC voltage on output pins is V_{CC} +0.5V, which may overshoot to V_{CC} +2.0V for periods of less than 20 ns.

P9E D

CATALYST SEMICONDUCTOR-

D.C. OPERATING CHARACTERISTICS

CAT64LC20 T_A= 0°C to +70°C, V_{CC} = +2.5V to +5.5V, unless otherwise specified. CAT64LC20l T_A= -40°C to +85°C, V_{CC} = +2.5V to +5.5V, unless otherwise specified.

| | | | | Limits Min. Typ. Max. | | | | |
|----------------------|---|--------|--------|-----------------------|-----|-----------------------|--|--|
| Sym. | Paramete | r | | | | Units | Test Conditions | |
| lcc | Operating Current | 2.5V | | | | 0.4 | mA | f _{SK} = 250 kHz |
| | EWEN, EWDS, READ | 5.5V | | | | 1.0 | | fsk = 1 MHz |
| ICCP | Program Current | 2.5V | | | | 2.0 | mA | · |
| | | 5.5V | | | | 3.0 |] [| |
| IsB | Standby Current | Stand | lard | | | 3.0 | μА | V _{IN} = GND or V _{CC} |
| I _{SBZ} (5) | | ZERC |) Pwr™ | | | 0 | 1 1 | $\overline{\text{CS}} = V_{\text{CC}}$ |
| ILI | Input Leakage Current | | | | 2.0 | μА | V _{IN} = GND to V _{CC} | |
| ILO | Output Leakage Curre | nt | | | | 10 | μΑ | Vour = GND to Vcc |
| VIL | Low Level Input Voltag | e, DI | | -0.1 | | V _{CC} x 0.3 | V | |
| VIH | High Level Input Voltag | ge, DI | | Vcc x 0.7 | | V _{CC} + 0.5 | V | |
| VIL | Low Level Input Voltag CS, SK, RESET | je, | | -0.1 | | V _{CC} x 0.2 | V | |
| V _{IH} | High Level Input Voltag | ge, | | V _{CC} x 0.8 | | V _{CC} + 0.5 | V | |
| VoH | High Level Output Volt | age | 2.5V | V _{CC} - 0.3 | | | ٧ | lон = −10μA |
| | | | 4.5V | V _{CC} - 0.3 | | | | lон = −10μA |
| | | | | 2.4 | | | | I _{OH} = -400μA |
| Vol | Low Level Output Volta | age | 2.5V | | | 0.4 | ٧ | l _{OL} = 10μΑ |
| | | Ī | 4.5V | | | | | l _{OL} = 2.1mA |

⁽⁵⁾ Standby Current (I_{SBZ}) = 0μA (<900nA)

CATALYST SEMICONDUCTOR-

Advance

A.C. OPERATING CHARACTERISTICS

CAT64LC20 T_A= 0°C to +70°C, V_{CC} = +2.5V to +5.5V, unless otherwise specified. CAT64LC20I T_A= -40°C to +85°C, V_{CC} = +2.5V to +5.5V, unless otherwise specified.

| | | | | Limits | | |
|---------------------|---------------------------------|-----------|--------|--------|------|-------|
| Symbol | Parameter | | Min. | Тур. | Max. | Units |
| toss | CS Setup Time | | 100 | | | ns |
| tcsн | CS Hold Time | | 100 | | | ns |
| tois | DI Setup Time | | 200 | | | ns |
| tDIH | DI Hold Time | | 200 | | | ns |
| t _{PD1} | Output Delay to 1 | | ··· ·· | | 300 | ns |
| t _{PD0} | Output Delay to 0 | | | | 300 | ns |
| t _{HZ} (6) | Output Delay to High Impendance | , | | | 500 | ns |
| tcsmin | Minimum CS High Time | | 250 | | | ns |
| tskHI | Minimum SK High Time | 2.5V | 1000 | | | ns |
| | | 4.5V-5.5V | 400 | | | |
| tsklow | Minimum SK Low Time | 2.5V | 1000 | | | ns |
| | | 4.5V-5.5V | 400 | | | |
| tsv | Output Delay to Status Valid | | | | 500 | ns |
| fsĸ | Maximum Clock Frequency | 2.5V | 250 | | | kHz |
| | | 4.5V-5.5V | 1000 | | | |
| tress | Reset to CS Setup Time | | 0 | | | ns |
| tresmin | Minimum RESET High Time | | 250 | | | ns |
| tresh | RESET to READY Hold Time | | 0 | | | ns |
| t _{RC} | Write Recovery | | 100 | | | ns |

POWER-UP TIMING(3)(7)

| Symbol | Parameter | Min. | Max. | Units |
|------------------|-------------------------------|------|------|-------|
| tpur | Power-Up to Read Operation | | 10 | μs |
| t _{PUW} | Power-Up to Program Operation | | 1 | ms |

WRITE CYCLE LIMITS

| Symbol | Parameter | | Min. | Max. | Units |
|--------|--------------------|-----------|------|------|-------|
| twR | Program Cycle Time | 2.5V | | 10 | ms |
| | | 4.5V-5.5V | | 5 | |

Note:

(3) This parameter is tested initially and after a design or process change that affects the parameter.

(6) This parameter is sampled but not 100% tested.

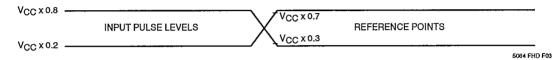
(7) tpuR and tpuW are the delays required from the time V_{CC} is stable until the specified operation can be initiated.

CATALYST SEMICONDUCTOR

INSTRUCTION SET

| Instruction | Opcode | Address | Data |
|--------------------------|----------|------------------------|--------|
| Read | 10101000 | A6 A5 A4 A3 A2 A1 A0 0 | D15-D0 |
| Write | 10100100 | A6 A5 A4 A3 A2 A1 A0 0 | D15-D0 |
| Write Enable | 10100011 | XXXXXXX | |
| Write Disable | 10100000 | xxxxxxxx | |
| [Write All Locations](8) | 10100001 | xxxxxxx | D15-D0 |

Figure 1. A.C. Testing Input/Output Waveform $^{(9)(10)(11)}$ (C_L = 100 pF)



- (8) (Write All Locations) is a test mode operation and is therefore not included in the A.C./D.C. Operations specifications.
 (9) Input Rise and Fall Times (10% to 90%) < 10 ns.
 (10) Input Pulse Levels = V_{CC} x 0.2 and V_{CC} x 0.8.
 (11) Input and Output Timing Reference = V_{CC} x 0.3 and V_{CC} x 0.7.

CATALYST SEMICONDUCTOR-

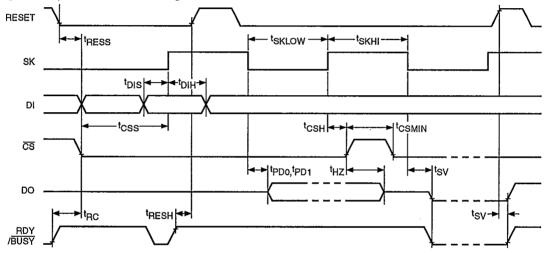
DEVICE OPERATION

The CAT64LC20/CAT64LC20I is a 2K bit nonvolatile memory intended for use with all standard controllers. The CAT64LC20/CAT64LC20I is organized in a 128 x 16 format. All instructions are based on an 8 bit format. There are four 16 bit instructions: READ, WRITE, EWEN, and EWDS. The CAT64LC20/CAT64LC20I operates on a single power supply ranging from 2.5V to 5.5V and it has an on-chip voltage generator to provide the high voltage needed during a programming operation. In-

structions, addresses and data to be written are clocked into the DI pin on the rising edge of the SK clock. The DO pin is normally in a high impedance state except when outputting data in a READ operation or outputting RDY/BUSY status when polled during a WRITE operation.

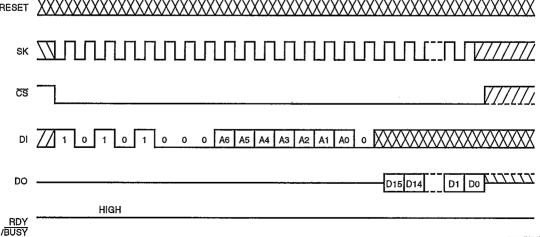
The format for all instructions sent to this device includes a 4 bit start sequence, 1010, a 4 bit op code and an 8 bit address field or dummy bits. For a WRITE operation, a





5064 FHD F04

Figure 3. Read Instruction Timing



5066 FHD F05

CATALYST SEMICONDUCTOR

16 bit data field is also required following the 8 bit address field.

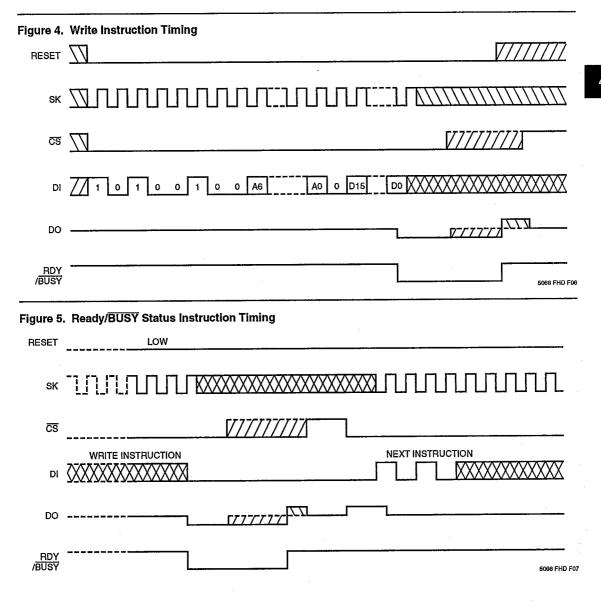
The CAT64LC20/CAT64LC20I requires an active LOW \overline{CS} in order to be selected. Each instruction must be preceded by a HIGH-to-LOW transition of \overline{CS} before the input of the 4 bit start sequence. Prior to the 4 bit start sequence (1010), the device will ignore inputs of all other logical sequence.

Read

Upon receiving a READ command and address (clocked into the DI pin), the DO pin will output data one t_{PD} after the falling edge of the 16th clock (the last bit of the address field). The READ operation is not affected by the RESET input.

Write

After receiving a WRITE op code, address and data, the device goes into the AUTO-Clear cycle and then the



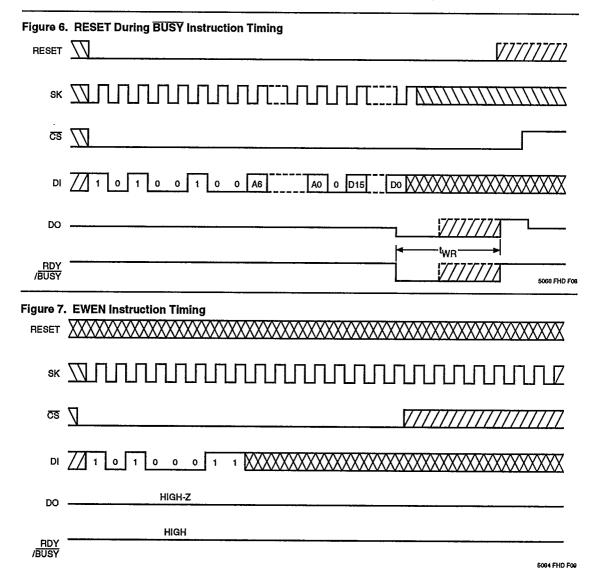
WRITE cycle. The RDY/BUSY pin will output the BUSY status (LOW) one tsy after the rising edge of the 32nd clock (the last data bit) and will stay LOW until the write cycle is complete. Then it will output a logical "1" until the next WRITE cycle. The RDY/BUSY output is not affected by the input of $\overline{\text{CS}}$.

An alternative to get RDY/BUSY status is from the DO pin. During a write cycle, asserting a LOW input to the CS pin will cause the DO pin to output the RDY/BUSY status. Bringing CS HIGH will bring the DO pin back to a high impedance state again. After the device has completed a WRITE cycle, the DO pin will output a

logical "1" when the device is deselected. The rising edge of the first "1" input on the DI pin will reset DO back to the high impedance state again.

The WRITE operation can be halted anywhere in the operation by the RESET input. If a RESET pulse occurs during a WRITE operation, the device will abort the operation and output a READY status.

NOTE: Data may be corrupted if a RESET occurs while the device is BUSY. If the reset occurs before the BUSY period, no writing will be initiated. However, if RESET occurs after the BUSY period, new data will have been written over the old data.



CATALYST SEMICONDUCTOR -

RESET

The RESET pin, when set to HIGH, will reset or abort a WRITE operation. When RESET is set to HIGH while the WRITE instruction is being entered, the device will not execute the WRITE instruction and will keep DO in High-Z condition.

When RESET is set to HIGH, while the device is in a clear/write cycle, the device will abort the operation and will display READY status on the RDY/BUSY pin and on the DO pin if CS is low.

The RESET input affects only the WRITE and WRITE ALL operations. It does not reset any other operations

Figure 8. EWDS Instruction Timing

such as READ, EWEN and EWDS.

ERASE/WRITE ENABLE and DISABLE

The CAT64LC20/CAT64LC20I powers up in the erase/ write disabled state. After power-up or while the device is in an erase/write disabled state, any write operation must be preceded by an execution of the EWEN instruction. Once enabled, the device will stay enabled until an EWDS has been executed or a power-down has occured. The EWDS is used to prevent any inadvertent overwriting of the data. The EWEN and EWDS instructions have no affect on the READ operation and are not affected by the RESET input.

HIGH-Z DO

HIGH RDY /BUSY

5064 FHO F10